



IXTP1R6N100D2 Information



For Reference Only

Part Number IXTP1R6N100D2

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 1000V 1.6A TO220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IXTP1R6N100D2 Specifications

Manufacturer Part Number IXTPIR6N100D2 Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 1.6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 27nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 645pF @ 25V Vgs (Max) ±20V FET Feature Depletion Mode Power Dissipation (Max) 100W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 800mA, 0V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ### 20V ### 30 (Max) @ Id, Vgs I 0 Ohm @ 800mA, 0V Operating Temperature ### 30 (Max) @ Id, Vgs I 0 Ohm @ 800mA, 0V Operating Temperature ### 30 (T) 20 (TI) ### 40 (Mounting Type	Manufacturer Part Number	IXTP1R6N100D2
Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 1.6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 27nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 645pF @ 25V Vgs (Max) ±20V FET Feature Depletion Mode Power Dissipation (Max) 100W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 800mA, 0V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer	IXYS
Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 1.6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 27nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 645pF @ 25V Vgs (Max) ±20V FET Feature Depletion Mode Power Dissipation (Max) 100W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 800mA, 0V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Category	Discrete Semiconductor Products
Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)1000VCurrent - Continuous Drain (Id) @ 25°C1.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id-Gate Charge (Qg) (Max) @ Vgs27nC @ 5VInput Capacitance (Ciss) (Max) @ Vds645pF @ 25VVgs (Max)±20VFET FeatureDepletion ModePower Dissipation (Max)100W (Tc)Rds On (Max) @ Id, Vgs10 Ohm @ 800mA, 0VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1000V Current - Continuous Drain (Id) @ 25°C 1.6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 27nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 645pF @ 25V Vgs (Max) ±20V FET Feature Depletion Mode Power Dissipation (Max) 100W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 800mA, 0V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case Tooks 1000 Too	Package	TO-220-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 1.6A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Depletion Mode Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 Ohm @ 800mA, 0V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Supplier Device Package Package / Case MOSFET (Metal Oxide) 1000V 100V 100V 10V 10V 10V 10V	Series	-
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Depletion Mode Power Dissipation (Max) Rds On (Max) @ Id, Vgs Doperating Temperature Operating Temperature Supplier Device Package Package / Case 1000V 100V	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **E20V FET Feature Depletion Mode Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 Ohm @ 800mA, 0V Operating Temperature Supplier Device Package Package / Case 1.6A (Tc) 1.6	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Depletion Mode Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 Ohm @ 800mA, 0V Operating Temperature Supplier Device Package Package / Case TO-220AB TO-220-3	Drain to Source Voltage (Vdss)	1000V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 645pF @ 25V Vgs (Max) ±20V FET Feature Depletion Mode Power Dissipation (Max) I00W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 800mA, 0V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	1.6A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 645pF @ 25V Vgs (Max) ±20V FET Feature Depletion Mode Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 Ohm @ 800mA, 0V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Depletion Mode Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 Ohm @ 800mA, 0V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	-
Vgs (Max)±20VFET FeatureDepletion ModePower Dissipation (Max)100W (Tc)Rds On (Max) @ Id, Vgs10 Ohm @ 800mA, 0VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	27nC @ 5V
FET Feature Depletion Mode Power Dissipation (Max) 100W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 800mA, 0V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	645pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 Ohm @ 800mA, 0V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs10 Ohm @ 800mA, 0VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	Depletion Mode
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	100W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	10 Ohm @ 800mA, 0V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

IXTP1R6N100D2 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTP1R6N100D2 Payment Methods



















IXTP1R6N100D2 Shipping Methods













If you have any question about IXTP1R6N100D2, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com